

**FIG. 3A**

FIG. 3A is a cross-sectional view of a substrate 100. A thin film layer 101 is formed on the top surface of the substrate 100. The thin film layer 101 is composed of two sub-layers, 101a and 101b, which are stacked on top of each other. The substrate 100 is shown with a break symbol (two wavy lines) on the left and right sides, indicating it is a partial view. A label 102 points to the top surface of the thin film layer 101.

**FIG. 3B**

FIG. 3B is a cross-sectional view of a second embodiment of the device. It shows a substrate with a central raised region. A layer 103 is on the top surface of the raised region, and a layer 107 is on the top surface of the substrate. A layer 104 is on the top surface of the raised region, and a layer 105 is on the top surface of the substrate. The layers 103 and 107 are shown as a single layer, and the layers 104 and 105 are shown as a single layer. The layers 103 and 104 are shown as a single layer, and the layers 107 and 105 are shown as a single layer. The layers 103 and 104 are shown as a single layer, and the layers 107 and 105 are shown as a single layer. The layers 103 and 104 are shown as a single layer, and the layers 107 and 105 are shown as a single layer.

FIG. 3C

FIG. 3C is a cross-sectional view of a semiconductor device. It shows a substrate with a trench. A conductive layer is formed on the top surface of the substrate and extends into the trench. The conductive layer is labeled 110. The trench is labeled 109. The substrate is labeled 108. The conductive layer 110 is shown as a thin layer on the top surface of the substrate 108, and it is also shown as a layer within the trench 109. The conductive layer 110 is shown as a thin layer on the top surface of the substrate 108, and it is also shown as a layer within the trench 109.

**FIG. 3E**

120c  
120b  
120a } 120